

|          |  |  |  | Sub | ject | t Code: KEC053 |  |  |  |  |  |  |
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## BTECH (SEM V) THEORY EXAMINATION 2023-24 VLSI TECHNOLOGY

TIME: 3 HRS M.MARKS: 100

Note: 1. Attempt all Sections. If require any missing data; then choose suitably.

| 1.         | SECTION A . Attempt <i>all</i> questions in brief.   |                          |                 |  |  |  |
|------------|--|--------------------------|-----------------|--|--|--|
| Qno.       | Question   | Marks                    | СО              |  |  |  |
| a.         | Mention the advantages of ICs.   | 2                        | 1               |  |  |  |
| b.         | Define polishing.  | 2                        | 1               |  |  |  |
| c.         | What is auto doping in growth process?   | 2                        | 2               |  |  |  |
| d.         | What is plasma oxidation?  | 2                        | 2               |  |  |  |
| e.         | Explain photo mask.  | 2                        | 3               |  |  |  |
| f.         | What are PR materials?   | 2                        | 3               |  |  |  |
| g.         | Write the types of diffusion.  | 2                        | 4               |  |  |  |
| h.         | Define ion-implantation  | 2                        | 4               |  |  |  |
| i.         | Enlist different types of IC packages.   | 2                        | 5               |  |  |  |
| j.         | Write all packaging design considerations.   | 2                        | 5               |  |  |  |
|            |  |                          | 1               |  |  |  |
|            | SECTION B  |                          | Ω.              |  |  |  |
| 2.         | Attempt any three of the following:  | 10 x 3                   | <del>=</del> 30 |  |  |  |
| a.         | Explain Electronic Grade Silicon with neat diagram   | 10                       | 1               |  |  |  |
| b.         | Discuss Vapor-Phase Epitaxy.   | 10                       | 2               |  |  |  |
| c.         | Explain in detail Optical Lithography.   | 10                       | 3               |  |  |  |
| d.         | Explain fick's law of diffusion.   | 10                       | 4               |  |  |  |
| e.         | Discuss Package Types and Packaging Design Considerations.   | 10                       | 5               |  |  |  |
|            | SECTION C  |                          |                 |  |  |  |
| 3.         | Attempt any <i>one</i> part of the following:  | 10 x 1 =                 | = 10            |  |  |  |
| a.         | Explain CZ process in detail with neat diagram. What is the pull rate in CZ                              | 10                       | 1               |  |  |  |
|            | technique?   | 10                       |                 |  |  |  |
| b.         | Discuss different shaping operations involved in preparing wafers with                                   | 10                       | 1               |  |  |  |
|            | diagram.   | 10 1                     |                 |  |  |  |
| 4.         | Attempt any one part of the following:   | 10 x 1 =                 |                 |  |  |  |
| a.         | Explain the principle of Molecular Beam Epitaxy.   | 10                       | 2               |  |  |  |
| b.         | What is latch up? How it is avoided in CMOS technology?  |                          |                 |  |  |  |
| 5.         | Attempt any <i>one</i> part of the following:  Explain the kinetics of wet watching. How gold is etched? | 10 x 1 =                 | 1               |  |  |  |
| a.<br>b.   | How is the silicon nitride used? Explain its deposition variables.                                       | 10                       | 3               |  |  |  |
| <b>6.</b>  | Attempt any one part of the following:   | $\frac{10}{10 \times 1}$ | _               |  |  |  |
|            | Define sheet resistance. Describe a method for its measurement.  | 10 x 1 -                 | 4               |  |  |  |
| a.<br>b.   | Discuss gaseous and liquid diffusion system.   | 10                       | 4               |  |  |  |
| 7 <b>.</b> | Attempt any one part of the following:   | 10 x 1 =                 | <u> </u>        |  |  |  |
| a.         | Explain Metallization and describe the problems associated with this process.                            | 10 x 1 -                 | <u> </u>        |  |  |  |
| c.         | 1 Daptem integration and describe the problems associated with tills process.                            | 10                       | J               |  |  |  |